

N-Ch and P-Ch Fast Switching MOSFETs

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

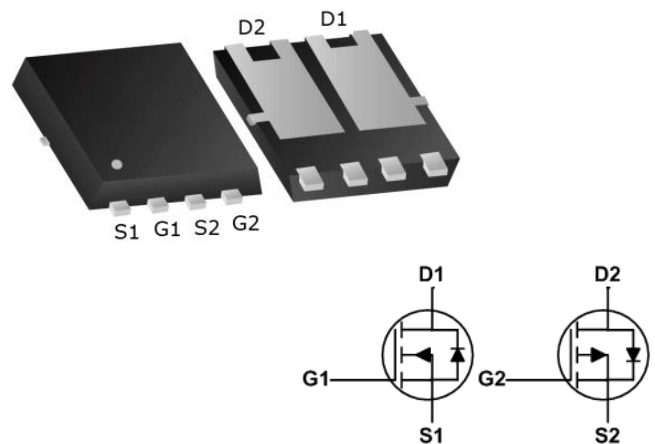


BVDSS	RDSON	ID
40V	11. m _Ω	40A
-40V	m _Ω	-40A

Description

The 5F is the high performance complementary N-ch and P-ch MOSFETs with high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications. The 5F meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

PDFN5060-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V _{DS}	Drain-Source Voltage	40	-40	V
V _{GS}	Gate-Source Voltage	± 20	± 20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	40	-40	A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	25	-21	A
I _{DM}	Pulsed Drain Current ²	80	-132	A
EAS	Single Pulse Avalanche Energy ³	66	156	mJ
I _{AS}	Avalanche Current	---	---	A
P _D @T _C =25°C	Total Power Dissipation ⁴	20	38	W
T _{STG}	Storage Temperature Range	-55 to 150	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹	---	60	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	3.3	°C/W

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N-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	40	---	---	V
$\Delta BV_{DSS} / \Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	---	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=1A$	---	11.5	15	$m\Omega$
		$V_{GS}=4.5V$, $I_D=1A$	---	14.1	18	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.0	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=40V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=40V$, $V_{GS}=0V$, $T_J=100^\circ\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=8A$	33	---	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	---	---	Ω
Q_g	Total Gate Charge	$V_{DS}=20V$, $V_{GS}=10V$, $I_D=8A$	---	22.9	---	nC
Q_{gs}	Gate-Source Charge		---	3.9	---	
Q_{gd}	Gate-Drain Charge		---	5.3	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{GS}=10V$, $V_{DD}=20V$, $R_G=3\Omega$, $I_D=10A$	---	5.5	---	ns
T_r	Rise Time		---	14	---	
$T_{d(off)}$	Turn-Off Delay Time		---	24	---	
T_f	Fall Time		---	12	---	
C_{iss}	Input Capacitance	$V_{DS}=20V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	964	---	pF
C_{oss}	Output Capacitance		---	109	---	
C_{rss}	Reverse Transfer Capacitance		---	96	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	40	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ\text{C}$	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $T_J=25^\circ\text{C}$, $V_{DD}=40V$, $V_G=10V$, $R_g=25\Omega$, $L=0.5\text{mH}$.
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

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P-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-40	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	---	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-1A$	---	17.5	23	$m\Omega$
		$V_{GS}=-4.5V$, $I_D=-1A$	---	24.5	32	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.2	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-40V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-40V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	-100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V$, $I_D=-5A$	---	12	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	4.3	---	Ω
Q_g	Total Gate Charge	$V_{DS}=-20V$, $V_{GS}=-10V$, $I_D=-5A$	---	30	---	nC
Q_{gs}	Gate-Source Charge		---	3	---	
Q_{gd}	Gate-Drain Charge		---	9	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-20V$, $V_{GS}=-10V$, $R_G=3.3\Omega$	---	9	---	ns
T_r	Rise Time		---	10	---	
$T_{d(off)}$	Turn-Off Delay Time		---	50	---	
T_f	Fall Time		---	20	---	
C_{iss}	Input Capacitance	$V_{DS}=-20V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1750	---	pF
C_{oss}	Output Capacitance		---	147	---	
C_{rss}	Reverse Transfer Capacitance		---	135	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	-40	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-13A$, $T_J=25^\circ\text{C}$	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F=-4A$, $di/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	24	---	nS
Q_{rr}	Reverse Recovery Charge		---	16	---	nC

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$ 3. The EAS data shows Max. rating. The test condition is $T_J=25^\circ\text{C}$, $V_{DD}=-40V$, $V_G=-10V$, $R_g=25\Omega$, $L=0.5\text{mH}$.4. The power dissipation is limited by 150°C junction temperature5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power

dissipation.

N-Ch and P-Ch Fast Switching MOSFETs

N-Channel Typical Characteristics

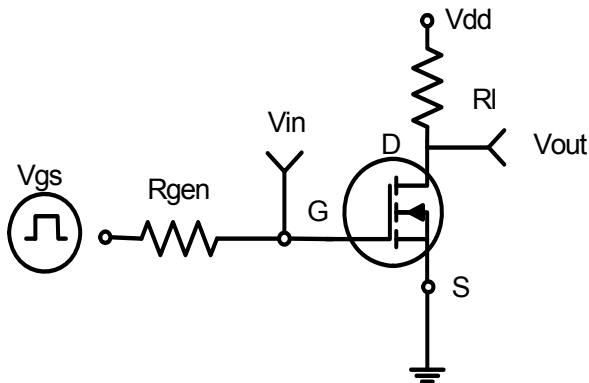


Figure 1: Switching Test Circuit

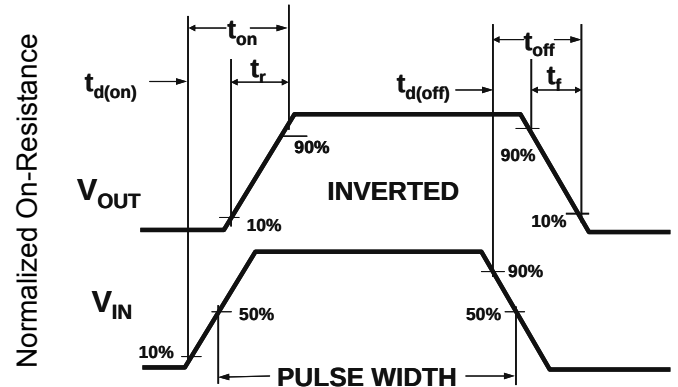
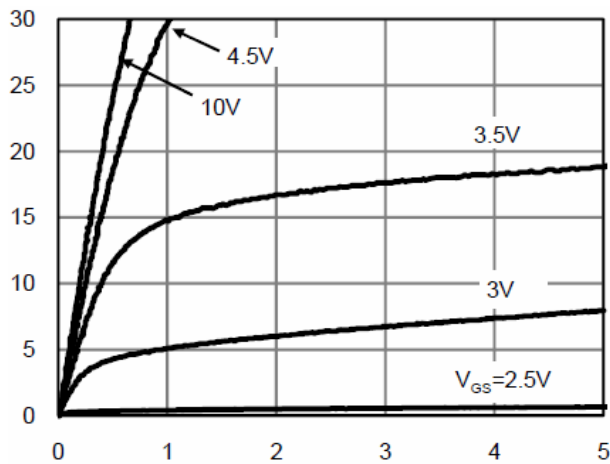
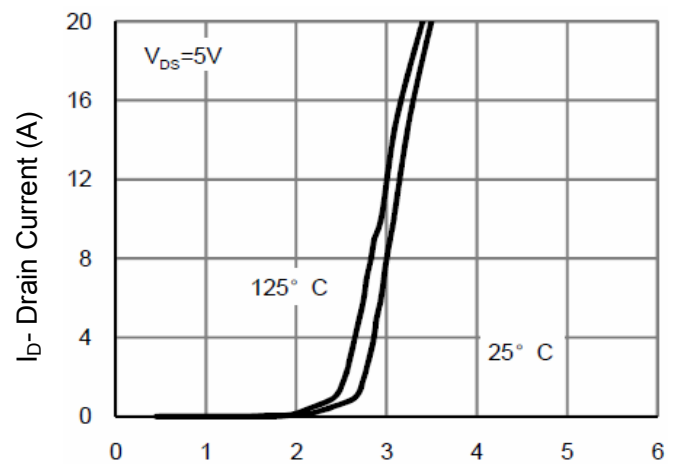


Figure 2: Switching Waveforms



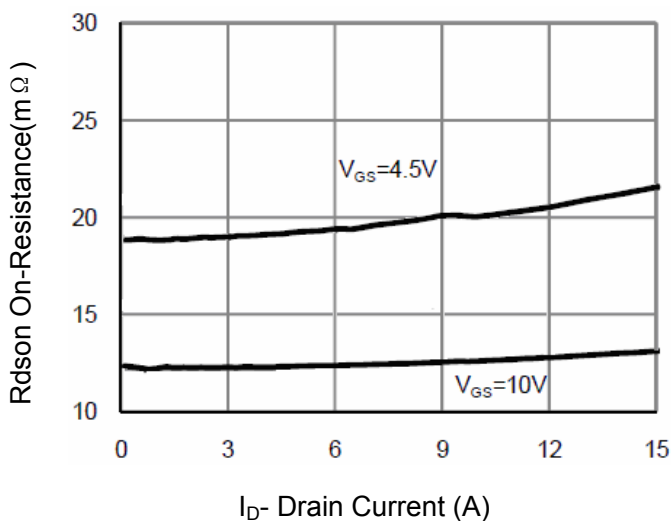
Vds Drain-Source Voltage (V)

Figure 3 Output Characteristics



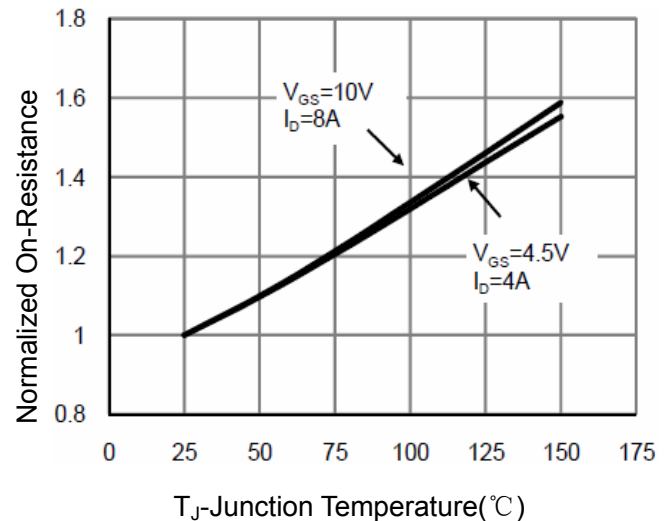
Vgs Gate-Source Voltage (V)

Figure 4 Transfer Characteristics



Id- Drain Current (A)

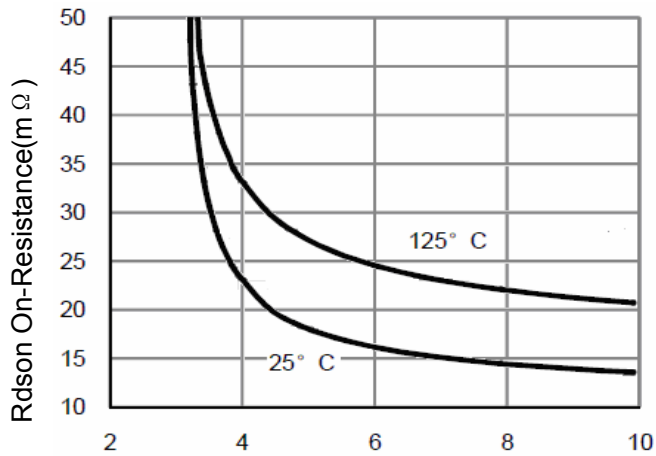
Figure 5 Drain-Source On-Resistance



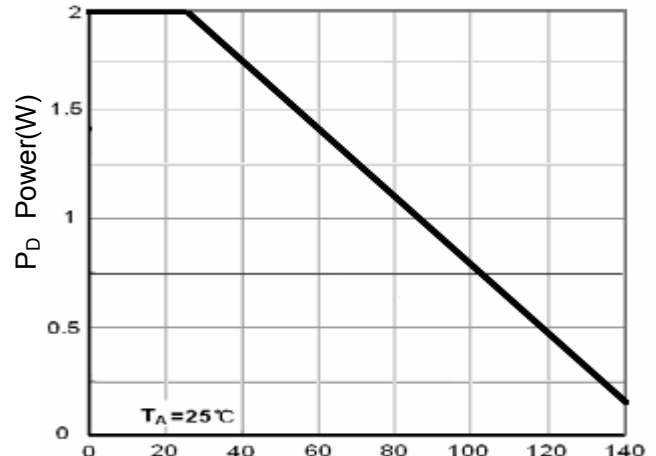
Tj-Junction Temperature(°C)

Figure 6 Drain-Source On-Resistance

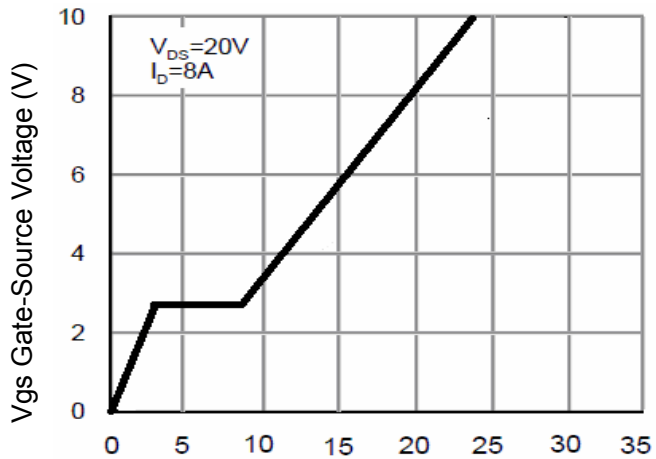
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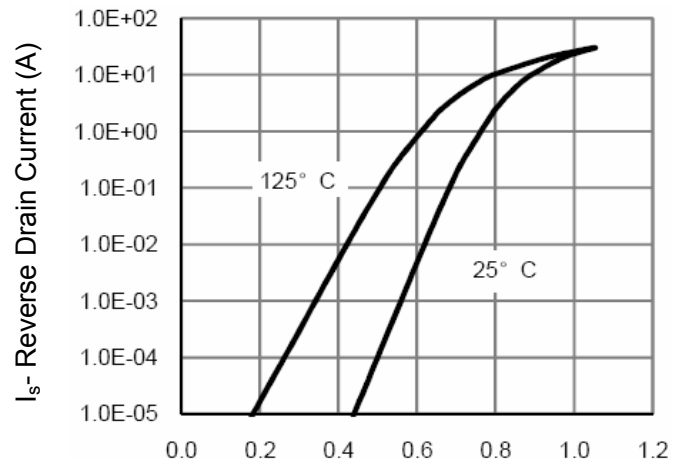
Vgs Gate-Source Voltage (V)
Figure 7 Rdson vs Vgs



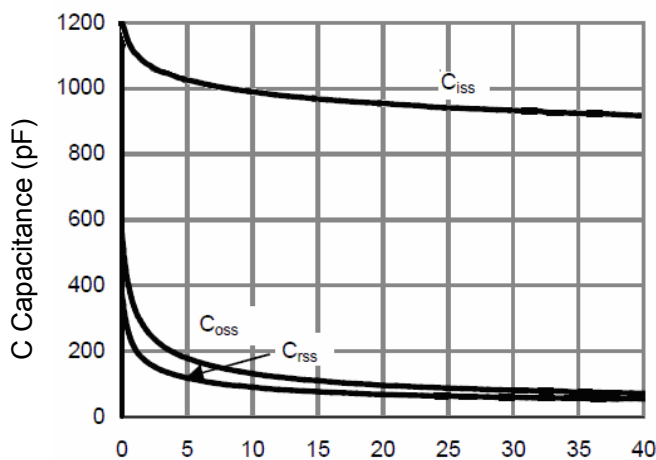
Tj Junction Temperature (°C)
Figure 8 Power Dissipation



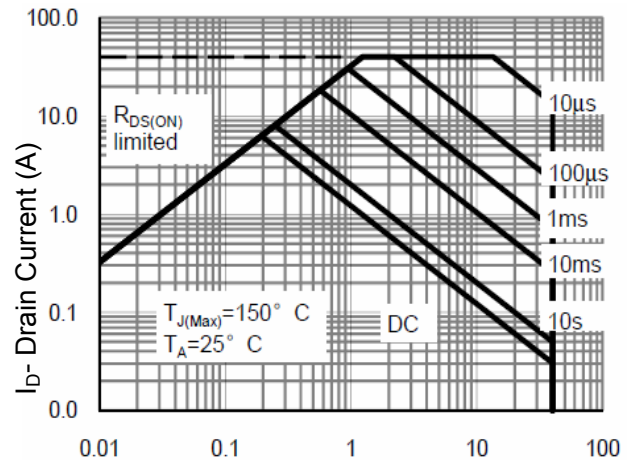
Qg Gate Charge (nC)
Figure 9 Gate Charge



Vds Drain-Source Voltage (V)
Figure 10 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)
Figure 11 Capacitance vs Vds



Vds Drain-Source Voltage (V)
Figure 12 Safe Operation Area

P-Channel Typical Characteristics

Figure 1. Output Characteristics

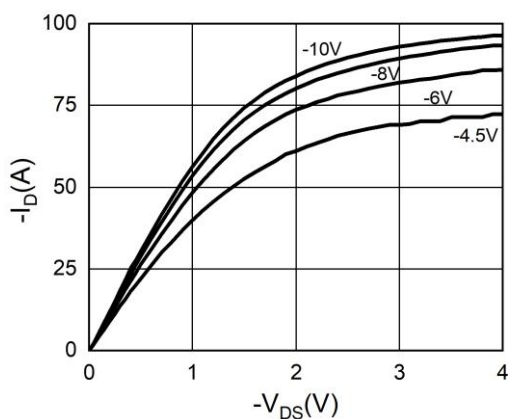


Figure 2. Transfer Characteristics

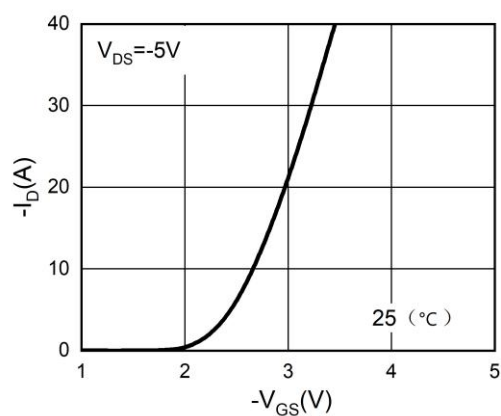


Figure 3. Power Dissipation

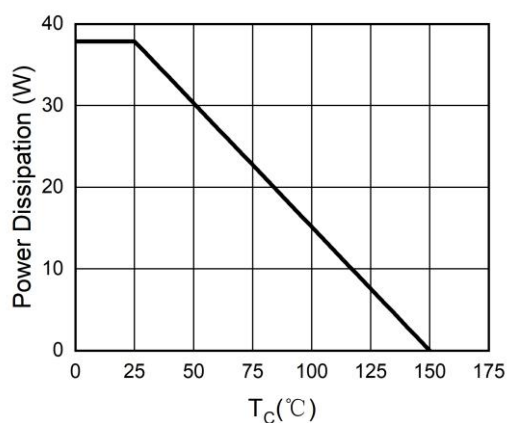


Figure 4. Drain Current

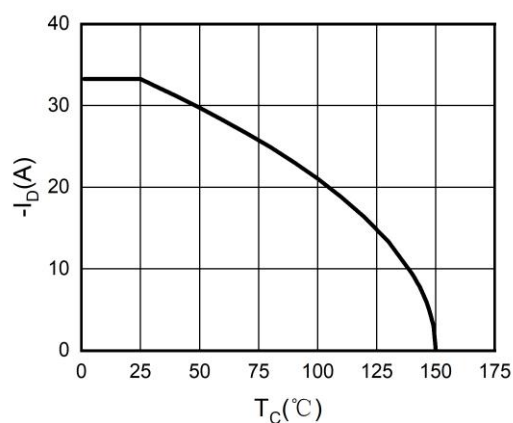


Figure 5. BV_{DSS} vs Junction Temperature

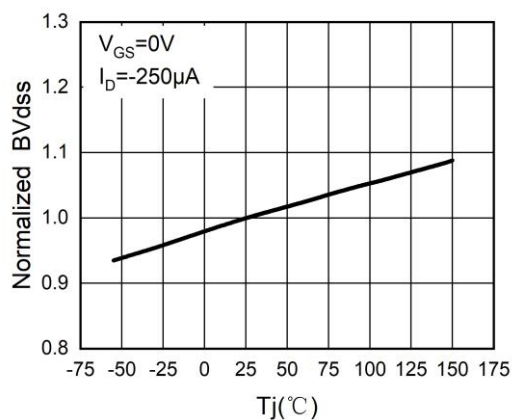


Figure 6. $R_{DS(ON)}$ vs Junction Temperature

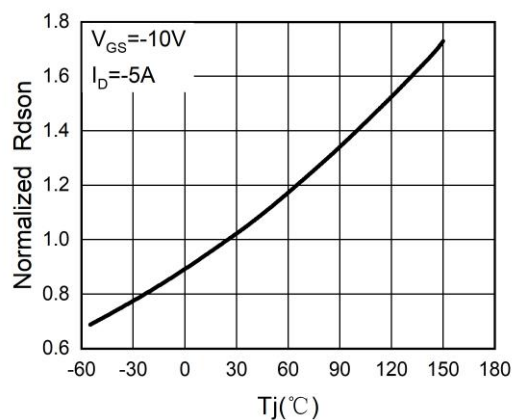


Figure 7. Gate Charge Waveforms

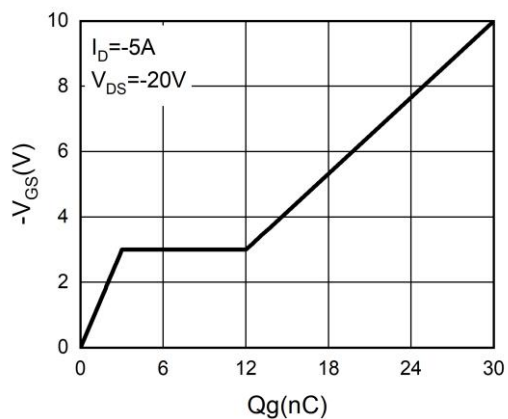


Figure 8. Capacitance

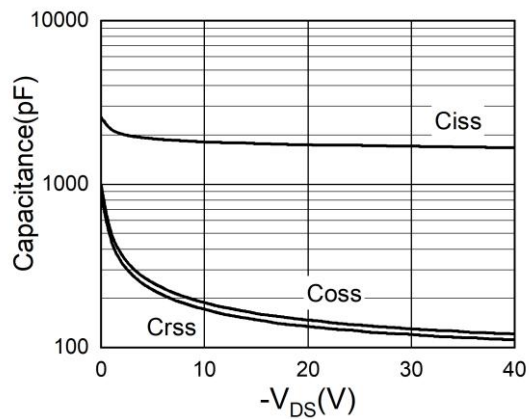


Figure 9. Body-Diode Characteristics

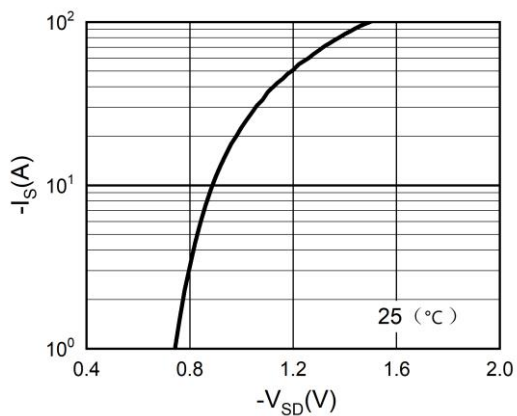


Figure 10. Maximum Safe Operating Area

